

WHAT IS CLAIMED IS:

1. A magnetization reversal method of applying an external magnetic field to a magnetoresistive film; wherein said magnetoresistive film has a structure in which a nonmagnetic film is placed between magnetic films with an easy axis of magnetization along a perpendicular direction to a film plane and wherein said external magnetic field comprises magnetic fields from a plurality of directions including a direction of the easy axis of magnetization of said magnetic films.
2. The magnetization reversal method according to Claim 1, wherein said magnetic field applied in said direction of the easy axis of magnetization comprises magnetic fields applied by a plurality of magnetic field applying means.
3. The magnetization reversal method according to Claim 1, wherein said magnetoresistive film further comprises a magnetic layer with greater longitudinal magnetic anisotropy than that of said magnetic films, between said magnetic film and the nonmagnetic film.
4. The magnetization reversal method according to Claim 3, wherein said magnetic film and said magnetic layer with greater longitudinal magnetic anisotropy are exchange-coupled with each other.

5. The magnetization reversal method according to
Claim 1, wherein said nonmagnetic layer is an
insulator.

5 6. The magnetization reversal method according to
Claim 1, wherein said external magnetic field comprises
magnetic fields generated by electric currents flowing
in conductor lines.

10 7. A magnetization reversal method of applying a
magnetic field from outside to a magnetic film to
change a direction of magnetization, wherein magnetic
fields are applied from a plurality of directions to
said magnetic film and intensities of the respective
15 magnetic fields are varied to effect reversal of
magnetization in said magnetic film.

20 8. The magnetization reversal method according to
Claim 7, wherein at least one magnetic field is a first
magnetic field applied with variation in intensity
during a period of complete reversal of magnetization
in said magnetic film and another magnetic field is a
second magnetic field applied in a fixed intensity and
thereafter retained in the intensity of the magnetic
25 field during the period of complete reversal of
magnetization in said magnetic film.

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9. The magnetization reversal method according to Claim 7, wherein an easy axis of magnetization of said magnetic film is a perpendicular direction to a film plane.

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10. The magnetization reversal method according to Claim 7, wherein said magnetic film has a structure in which a nonmagnetic layer is placed between a plurality of magnetic layers.

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11. The magnetization reversal method according to Claim 10, wherein said magnetic film is a magnetoresistive film.

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12. The magnetization reversal method according to Claim 10, wherein said magnetic layer has an easy axis of magnetization along a perpendicular direction to a film plane.

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13. The magnetization reversal method according to Claim 12, wherein a magnetic layer with greater longitudinal magnetic anisotropy than that of said magnetic layers is further placed between said magnetic layer and said nonmagnetic layer.

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14. The magnetization reversal method according to Claim 8, wherein said second magnetic field is

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applied in a direction of easy magnetization of said magnetic film.

15. The magnetization reversal method according
5 to Claim 14, wherein said plurality of applying
directions of the magnetic fields include a direction
inclined from the direction of easy magnetization of
said magnetic film, the magnetic fields are
simultaneously applied in the direction of easy
10 magnetization of said magnetic film and in the
direction inclined from the easy axis of magnetization,
the application of the magnetic field in the direction
inclined from the easy axis of magnetization is first
stopped, and thereafter the application of the magnetic
15 field in the direction of easy magnetization is
stopped.

16. The magnetization reversal method according
to Claim 7, wherein said magnetic fields are magnetic
20 fields generated by electric currents flowing in
conductor lines.

17. A magnetization reversal method of applying a
magnetic field from outside to a magnetic film with an
25 easy axis of magnetization along a perpendicular
direction to a film plane to change a direction of
magnetization, wherein said magnetic field applied is a

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magnetic field from a direction inclined from the easy axis of magnetization of said magnetic film.

18. The magnetization reversal method according
5 to Claim 17, wherein said magnetic film is a magneto resistive film in which a nonmagnetic layer is placed between a plurality of magnetic layers.

19. The magnetization reversal method according
10 to Claim 17, wherein said magnetic field is a magnetic field generated by an electric current flowing in a conductor line.

20. A magneto resistive film comprising a first magnetic film and a second magnetic film with an easy axis of magnetization along a perpendicular direction to a film plane, and having a structure in which a nonmagnetic layer is placed between said first magnetic film and second magnetic film,

20 wherein a magnetization reversal magnetic field of said first magnetic film < a magnetization reversal magnetic field of said second magnetic film, and wherein said second magnetic film undergoes reversal of magnetization by simultaneously applying the
25 magnetization reversal magnetic field of said first magnetic film and a magnetic field inclined from the easy axis of magnetization.

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21. The magnetoresistive film according to Claim 20, wherein a direction of the magnetic field inclined from the easy axis of magnetization is a longitudinal direction in the film plane of said magnetic film.

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22. The magnetoresistive film according to Claim 20, further comprising a magnetic layer with greater longitudinal magnetic anisotropy than that of said second magnetic film, between said second magnetic film and said nonmagnetic layer.

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23. The magnetoresistive film according to Claim 22, wherein said magnetic layer and said magnetic layer with greater longitudinal magnetic anisotropy are exchange-coupled with each other.

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24. The magnetoresistive film according to Claim 20, wherein said first and/or second magnetic film is a ferrimagnetic material.

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25. A magnetoresistive film comprising a first magnetic film and a second magnetic film with an easy axis of magnetization along a perpendicular direction to a film plane, and having a structure in which a nonmagnetic film is placed between said first magnetic film and said second magnetic film,

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wherein said first magnetic film undergoes

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reversal of magnetization by applying a magnetic field
in a direction of the easy axis of magnetization and a
magnetic field in a direction inclined from the easy
axis of magnetization, and wherein said second magnetic
5 film does not undergo reversal of magnetization by the
magnetic fields applied to said first magnetic film.

26. The magnetoresistive film according to Claim
25, wherein the magnetic field in the direction
10 inclined from the easy axis of magnetization is applied
in a longitudinal direction in the film plane of said
magnetic film.

27. The magnetoresistive film according to Claim
15 25, further comprising a magnetic layer with greater
longitudinal magnetic anisotropy than that of said
first magnetic film, between said first magnetic film
and said nonmagnetic film.

20 28. The magnetoresistive film according to Claim
27, wherein said first magnetic film and said magnetic
layer with greater longitudinal magnetic anisotropy are
exchange-coupled with each other.

25 29. The magnetoresistive film according to Claim
25, wherein said first and/or second magnetic film is a
ferrimagnetic material.

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30. A magnetic memory comprising:
a substrate;
a magnetoresistive film provided on the substrate,
which has a structure in which a nonmagnetic layer is
5 placed between a plurality of magnetic films with an
easy axis of magnetization along a perpendicular
direction to a film plane;
a write line for applying a magnetic field to said
magnetoresistive film; and
10 a bit line provided on the opposite side to said
substrate with respect to the magnetoresistive film,
wherein magnetization in at least one magnetic
film of said magnetoresistive film is reversed by
magnetic fields generated by electric currents flowing
15 in said write line and in said bit line.

31. A magnetic memory comprising:
a substrate;
a magnetoresistive film provided on the substrate,
20 which has a structure in which a nonmagnetic layer is
placed between a plurality of magnetic films with an
easy axis of magnetization along a perpendicular
direction to a film plane;
a write line for applying a magnetic field to said
25 magnetoresistive film; and
a bit line provided on the opposite side to said
substrate with respect to the magnetoresistive film,

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wherein the magnetic field from said write line is applied in a direction of the easy axis of magnetization of said magnetic films of said magnetoresistive film and a magnetic field from said bit line is applied in a direction inclined from the easy axis of magnetization.

32. The magnetic memory according to Claim 30 or 31, wherein said nonmagnetic film is an insulator.

33. The magnetic memory according to Claim 30 or 31, wherein said write line is shared between adjacent magnetoresistive films.

34. The magnetic memory according to Claim 30 or 31, further comprising a magnetic layer with greater longitudinal magnetic anisotropy than that of said magnetic film, between said magnetic film and nonmagnetic layer.

35. The magnetic memory according to Claim 34, wherein said magnetic film and said magnetic layer with greater longitudinal magnetic anisotropy are exchange-coupled with each other.

36. The magnetic memory according to either one of Claims 30, 31, and 34, wherein said magnetoresistive

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film is a magnetoresistive film in which at least one magnetic film undergoes reversal of magnetization by a magnetic field in a direction of the easy axis of magnetization and in which another magnetic film

5 undergoes reversal of magnetization by applying both the magnetic field in the direction of the easy axis of magnetization and the magnetic field inclined from the direction of the easy axis of magnetization,

wherein recording of information is implemented by
10 applying the magnetic field in the direction of the easy axis of magnetization and the magnetic field in the direction inclined from the direction of the easy axis of magnetization, and reproduction of information is implemented by applying only the magnetic field in
15 the direction of the easy axis of magnetization.

37. The magnetic memory according to either one of Claims 30, 31, and 34, wherein said magnetoresistive film is a magnetoresistive film in which at least one magnetic film undergoes reversal of magnetization by applying the magnetic fields in the direction of the easy axis of magnetization and in the direction inclined from the direction of the easy axis of magnetization and in which another magnetic film does not undergo reversal of magnetization even by applying the same magnetic fields,

wherein recording and/or reproduction of

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information is implemented by applying the magnetic fields in the direction of the easy axis of magnetization and in the direction inclined from the easy axis of magnetization.

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38. The magnetic memory according to Claim 30 or 31, wherein a plurality of magnetoresistive films are arrayed in a matrix pattern on said substrate.

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39. The magnetic memory according to Claim 38, wherein during recording of information, electric currents are made to flow in said bit line and in said write line to apply magnetic fields, thereby selecting a magnetoresistive film.

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40. The magnetic memory according to Claim 39, wherein the bit line for selection of the magnetoresistive film is a bit line connected to an adjacent magnetoresistive film.

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41. The magnetic memory according to Claim 39, wherein the bit line for selection of the magnetoresistive film is a bit line connected to the magnetoresistive film to be selected.

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42. The magnetic memory according to Claim 39, wherein the magnetic field from said bit line has a

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longitudinal component in the film plane of said magnetoresistive film.

43. The magnetic memory according to Claim 39,
5 wherein the magnetic field from said bit line has a component along the direction of the easy axis of magnetization of said magnetoresistive film.

44. The magnetic memory according to Claim 39,
10 further comprising a transistor connected to said magnetoresistive film.

45. The magnetic memory according to Claim 44,
wherein said magnetoresistive film is formed
15 immediately above a drain region of said transistor.

46. The magnetic memory according to Claim 45,
wherein a source electrode line connected to a source
region of said transistor also serves as said write
20 line.

47. A magnetic memory comprising:
a substrate;
a magnetoresistive film formed on the substrate,
25 which has a structure in which a nonmagnetic layer is placed between magnetic films with an easy axis of magnetization along a perpendicular direction to a film

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plane;

a write line for applying a magnetic field to said magnetoresistive film; and

5 a bit line provided on the opposite side to said substrate with respect to said magnetoresistive film,

said magnetic memory comprising means for applying an external magnetic field to the magnetic films of said magnetoresistive film while varying an intensity or a direction of the external magnetic field.

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48. The magnetic memory according to Claim 47, wherein said nonmagnetic film is an insulator.

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49. The magnetic memory according to Claim 47, wherein said write line is shared between adjacent magnetoresistive films.

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50. The magnetic memory according to Claim 47, wherein said magnetoresistive film is placed so that magnetic fields from said write line and bit line are applied in the direction of the easy axis of magnetization and in a direction inclined from the direction of the easy axis of magnetization to said magnetoresistive film.

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51. The magnetic memory according to Claim 50, further comprising a magnetic layer with greater

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longitudinal magnetic anisotropy than that of said magnetic film, between said magnetic film and nonmagnetic layer.

5 52. The magnetic memory according to Claim 51, wherein the direction inclined from the easy axis of magnetization is a longitudinal direction in the film plane of said magnetic film and wherein during recording of information, application of the magnetic field in the longitudinal direction is first stopped and thereafter the application of the magnetic field in the direction of the easy axis of magnetization is stopped.

15 53. A magnetic memory comprising:
a substrate;
magnetoresistive films formed in a matrix pattern on the substrate;
a write line for applying a magnetic field to said magnetoresistive films; and
20 a bit line provided on the opposite side to said substrate with respect to said magnetoresistive films, wherein in said magnetoresistive films, a first magnetic film, a second magnetic film, a nonmagnetic film, a third magnetic film, and a fourth magnetic film are stacked in the order named, at least the first and 25 fourth magnetic films have their easy axis of

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magnetization along a perpendicular direction to a film plane, and said second and third magnetic films have greater longitudinal magnetic anisotropy than that of said first and second magnetic films.

5 wherein at the same time as the magnetic field is applied in a direction of easy magnetization of said first and second magnetic films from said write line, a magnetic field is applied in a direction inclined from the easy axis of magnetization from said bit line,
10 thereby selecting a specific magnetoresistive film.

54. A magnetic memory comprising:
a substrate, and a plurality of magnetoresistive
films formed in a matrix pattern on the substrate, said
15 magnetoresistive films each having a structure in which
a nonmagnetic layer is placed between magnetic films
with an easy axis of magnetization along a
perpendicular direction to a film plane;
a write line for applying a magnetic field to said
20 magnetoresistive films; and
a bit line on the opposite side to said substrate
with respect to said magnetoresistive films,
wherein the magnetic field from said write line
and a magnetic field from said bit line are
25 simultaneously applied, application of the magnetic
field from the bit line is first stopped, and
thereafter application of the magnetic field from the

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write line is stopped after magnetization of said
magnetoresistive films has been aligned in the
direction of the magnetic field from said write line,
thereby implementing recording or reproduction of
information.

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